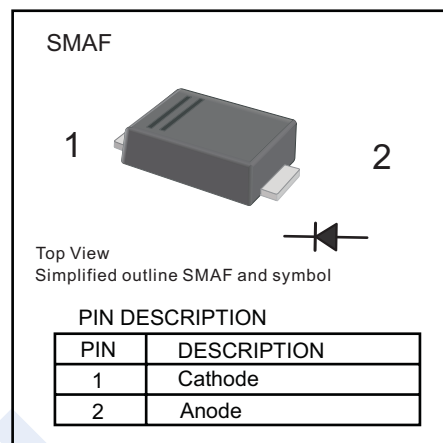


Rectifier Diodes

RR2LAM4S

■ Features

- Low forward voltage
- High current overload capacity

■ Absolute Maximum Ratings ($T_i = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage (Duty ≤ 0.5)	V_{RM}	400	V
Reverse voltage	V_R	400	
Average forward rectified current ^{*1}	I_O	2	A
Non-repetitive forward surge current ^{*2}	I_{FSM}	50	
Junction to lead, Thermal resistance	$R_{th(j-l)}$	25	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	

* 1 Glass epoxy board mounted, 60Hz half sin wave, resistive load, $T_i=90^\circ\text{C}$

* 2 60Hz half sin wave, non-repetitive at $T_j=25^\circ\text{C}$

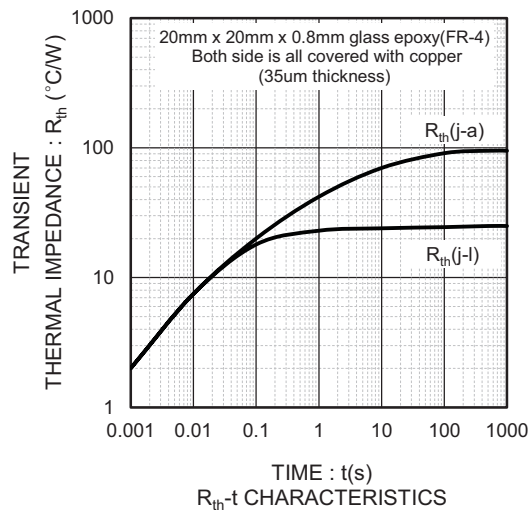
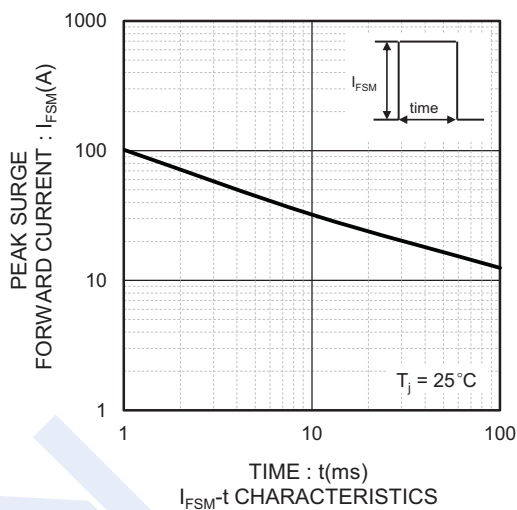
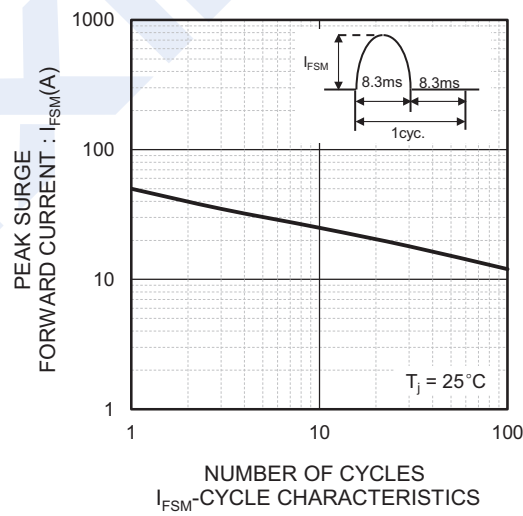
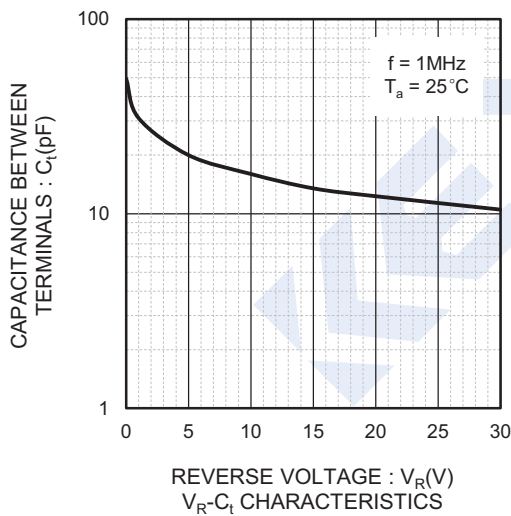
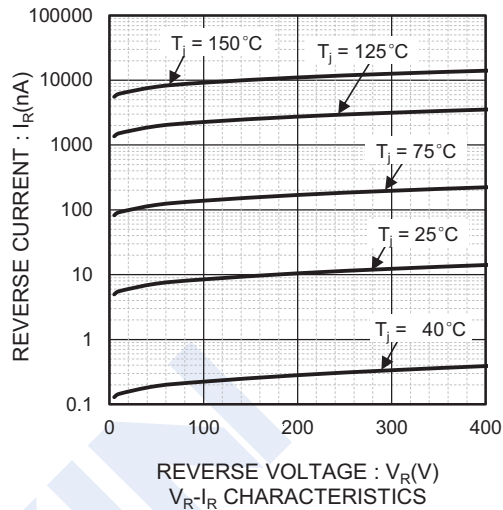
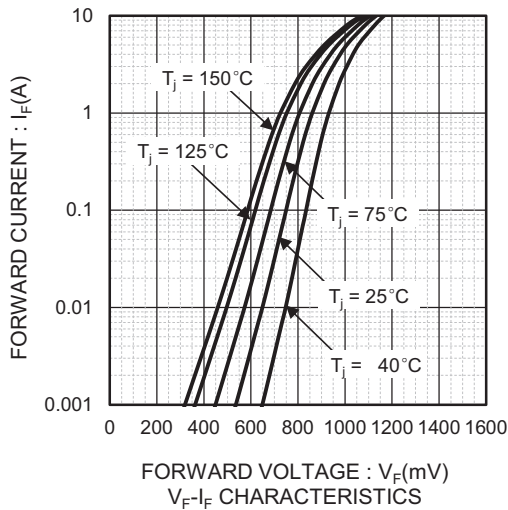
■ Electrical Characteristics ($T_j = 25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=2\text{A}$	0.75	0.9	1.1	V
Reverse current	I_R	$V_R=400\text{V}$			10	μA

Rectifier Diodes

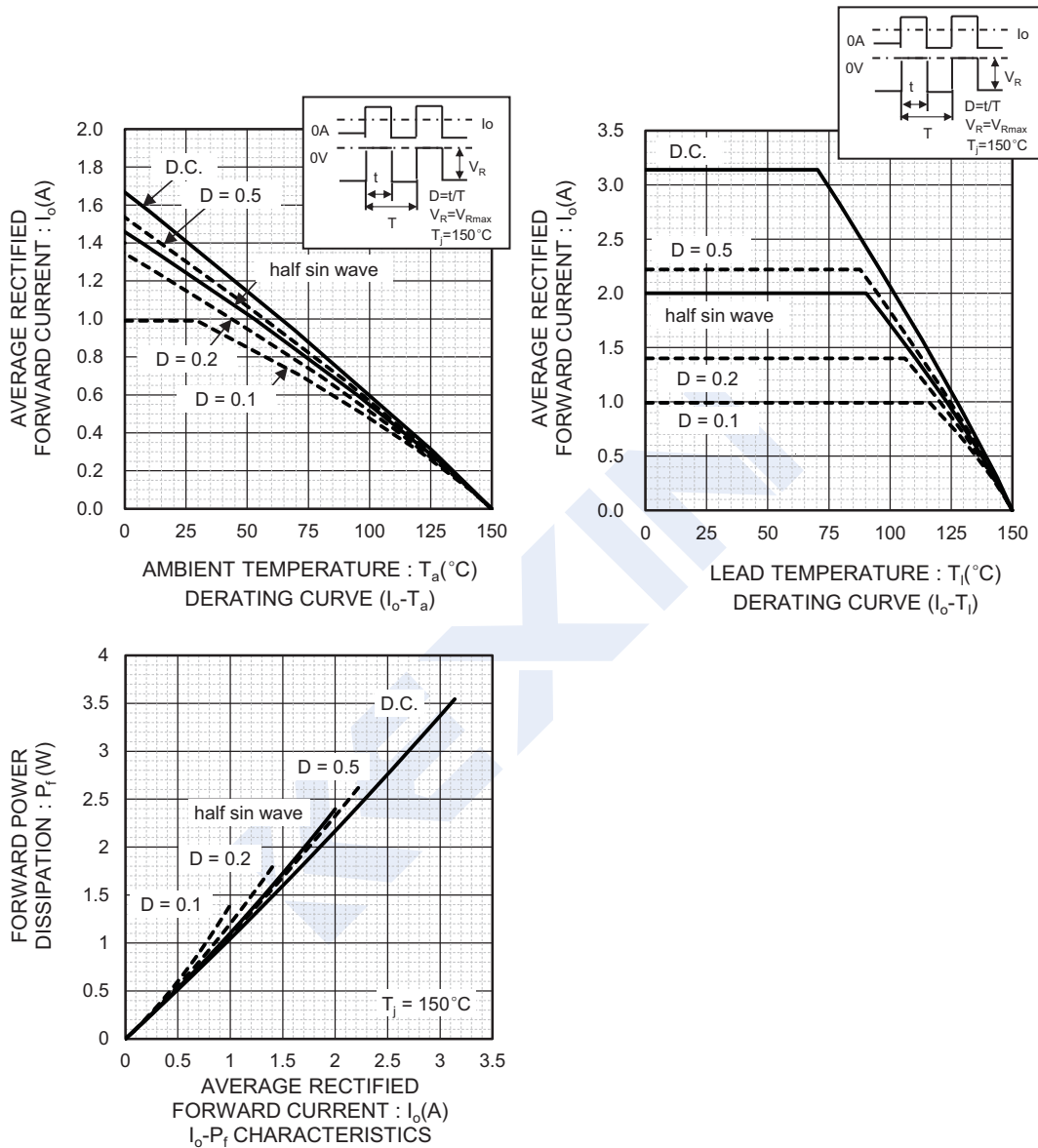
RR2LAM4S

Typical Characteristics



Rectifier Diodes

RR2LAM4S



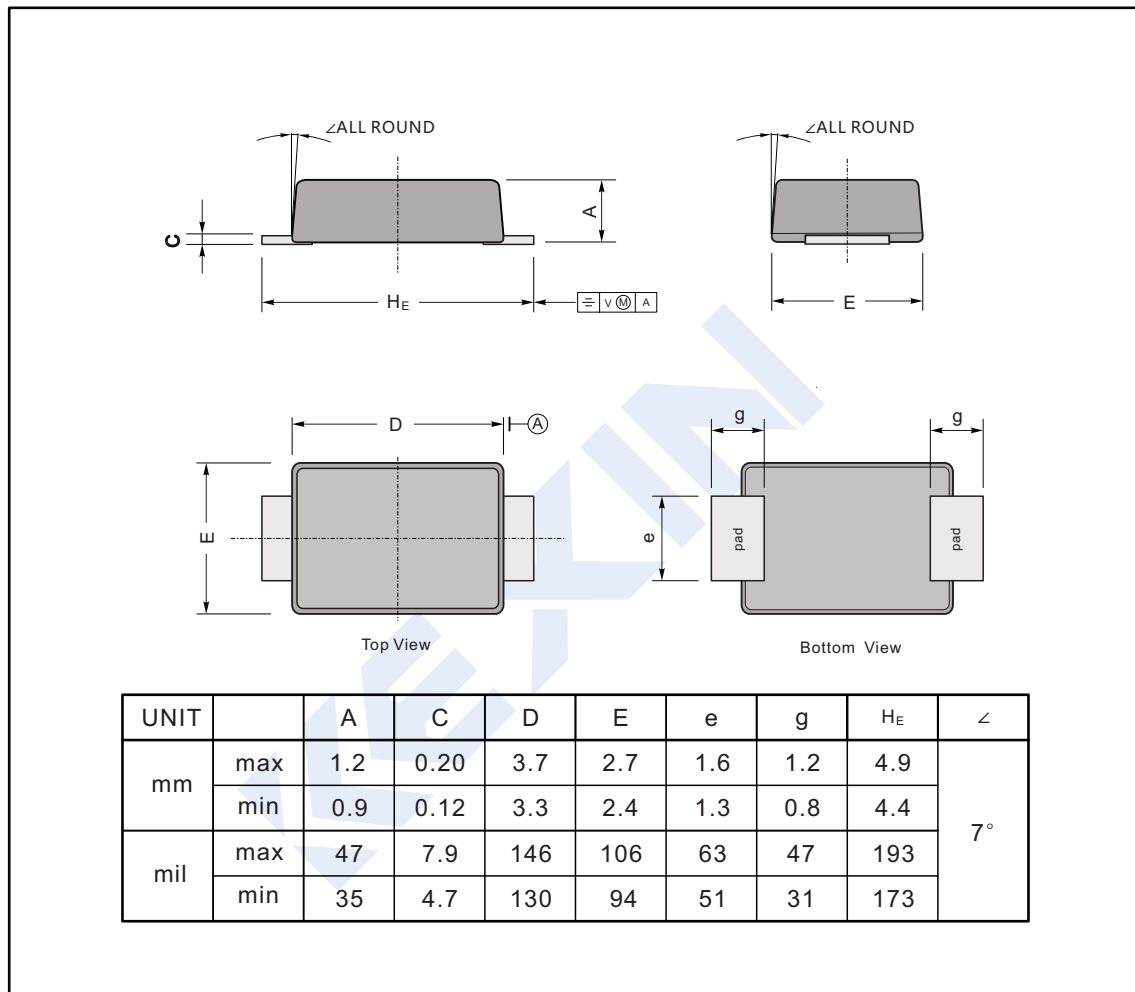
Rectifier Diodes

RR2LAM4S

■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SMAF



■ The recommended mounting pad size

